### SILICON (Si) POWER MOSFET A CEC3P07A

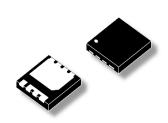


CET MOS

# CEC3P07A

# -30V ▲ 8mΩ ▲ -37A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type P-channel enhancement mode UL94V-0 rated flame retardant epoxy DFN3x3 package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability





RoHS

REACH

## **MAXIMUM RATINGS**

Parameter ( $T_A = 25^{\circ}C$ , unless otherwise noted)	Characteristics			
Drain-Source Voltage	V <sub>DS</sub>	-30V		
Gate-Source Voltage	V <sub>GS</sub>	±20V		
Continuous Drain Current at R <sub>TH_JC</sub>	I <sub>D</sub>	-37A at T <sub>c</sub> = 25°C	-23A at T <sub>c</sub> = 100°C	
Continuous Drain Current at R <sub>TH_JA</sub>	I <sub>D</sub>	-11A at T <sub>A</sub> = 25°C	-7A at T <sub>A</sub> = 100°C	
Pulsed Drain Current at R <sub>TH_JC</sub> Note 1	I <sub>DM</sub>	-148A at T <sub>c</sub> = 25°C		
Pulsed Drain Current at R <sub>TH_JA</sub> Note 1	I <sub>DM</sub>	-44A at T <sub>A</sub> = 25°C		
Maximum Power Dissipation	PD	25W at T <sub>c</sub> = 25°C	2.5W at T <sub>A</sub> = 25°C	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C		

# THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case Note 2	R <sub>TH_JC</sub>	5°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>th_ja</sub>	50°C/W

# **APPLICATIONS**

DC/DC	DC	Load	Power	USB
Converter	Fan	Switches	Banks	Storage
	$\bigcirc$		4	Y

# **PIN DESCRIPTION**

Circuit Diagram	Outline - Bottom View	Pin No.	Description
G (4) S (1,2,3)		1 2 3 4 5	Source Source Gate Drain

CEC3P07A 🛦 Rev.001 🛦 Date: 30/09/2022 🛦 Page: 1

Copyright by MGT A www.mgt.co.com All rights reserved The information in this document is subject to change without notice.



# **ELECTRICAL CHARACTERISTICS A** T<sub>A</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250 \mu A$	BV <sub>DSS</sub>	-30			V
Zero Gate Voltage Drain Current	$V_{DS}$ = -30V, $V_{GS}$ = 0V	I <sub>DSS</sub>			-1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V$ , $V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS}$ = -20V, $V_{DS}$ = 0V	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	V <sub>GS(th)</sub>	-1		-3	V
Static Drain-Source On-Resistance	$V_{GS} = -10V$ , $I_{D} = -10A$	R <sub>DS(ON)</sub>		8	10	mΩ
Static Drain-Source On-Resistance	$V_{GS} = -4.5V, I_{D} = -5A$	R <sub>DS(ON)</sub>		11.5	15	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1MHz	C <sub>ISS</sub>		2020		рF
Output Capacitance	$V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1MHz	Coss		390		pF
Reverse Transfer Capacitance	$V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		170		pF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = -10V, $I_{\text{D}}$ = -10A, $R_{\text{G}(\text{ext})}$ = $6\Omega$	t <sub>D(ON)</sub>		18		ns
Turn-On Rise Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = -10V, $I_{\text{D}}$ = -10A, $R_{G(\text{ext})}$ = $6\Omega$	t <sub>R</sub>		8		ns
Turn-Off Delay Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = -10V, $I_{\text{D}}$ = -10A, $R_{G(\text{ext})}$ = $6\Omega$	$t_{D(OFF)}$		108		ns
Turn-Off Fall Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = -10V, $I_{\text{D}}$ = -10A, $R_{G(\text{ext})}$ = $6\Omega$	t <sub>F</sub>		31		ns
Total Gate Charge	$V_{DS}$ = -15V, $V_{GS}$ = -5V, $I_D$ = -10A	$Q_{G}$		24		nC
Gate Source Charge	$V_{DS}$ = -15V, $V_{GS}$ = -5V, $I_D$ = -10A	Q <sub>GS</sub>		7		nC
Gate Drain Charge	$V_{DS}$ = -15V, $V_{GS}$ = -5V, $I_{D}$ = -10A	$\mathbf{Q}_{GD}$		10		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current <sup>Note 2</sup>		Is			-2.5	A
Drain-Source Diode Forward Voltage <sup>Note 3</sup>	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A	$V_{\text{SD}}$			-1	V

#### Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board,  $t \le 10$  sec.

CEC3P07A A Rev.001 A Date: 30/09/2022 A Page: 2

3: Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4: Guaranteed by design, not subject to production testing.

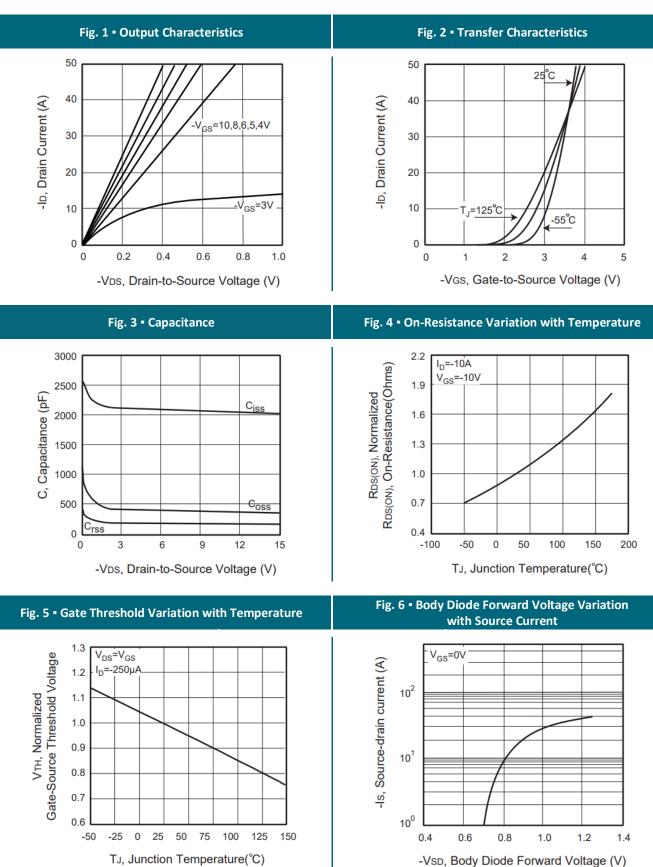


MGT 

Manufacturer Group of Technology

CET MOS

# **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**

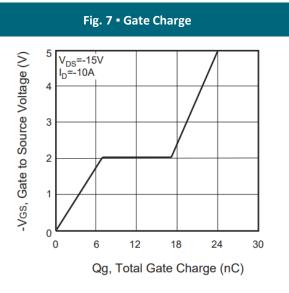


CEC3P07A A Rev.001 A Date: 30/09/2022 A Page: 3

Copyright by MGT **A** www.mgt.co.com **A** All rights reserved **A** The information in this document is subject to change without notice.



# **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**



#### Fig. 9 - Breakdown Voltage Variation vs. Temperature

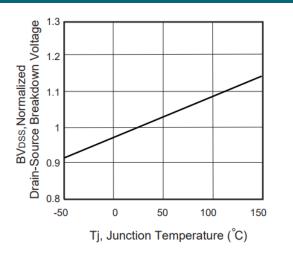
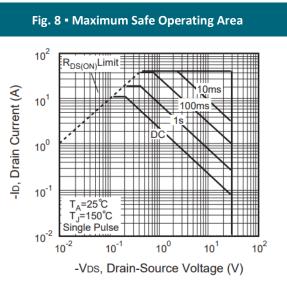
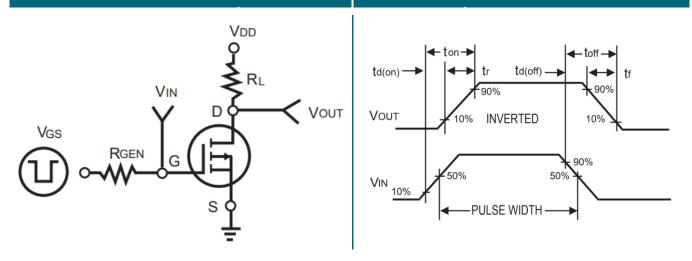


Fig. 10 • Switching Test Circuit



#### Fig. 11 - Switching Waveforms

MGT **A** Manufacturer Group of Technology

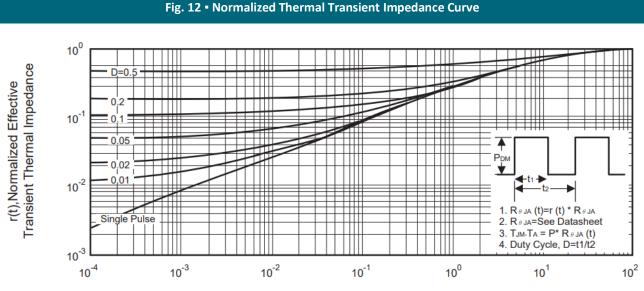


CEC3P07A A Rev.001 A Date: 30/09/2022 A Page: 4

Copyright by MGT A www.mgt.co.com All rights reserved The information in this document is subject to change without notice.

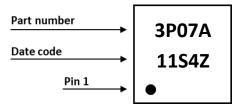


# **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**



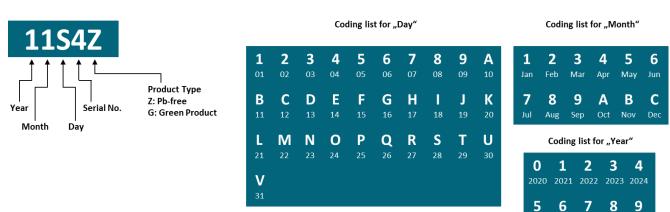
Square Wave Pulse Duration (sec)

# PART MARKING



# DATE CODE

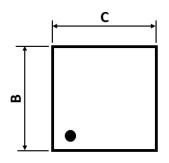
## Example: 11S4Z

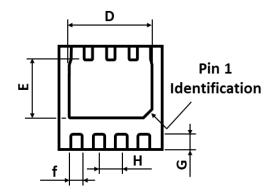


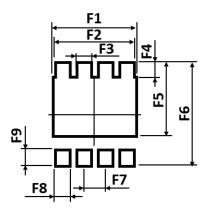
2025 2026 2027 2028 2029

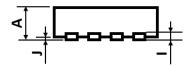


# PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	0.700	-	0.850	f	0.300	-	0.400
В	2.900	-	3.100	G	0.350	-	0.480
С	2.900	-	3.100	Н		0.650 (BSC)	
D	2.350	-	2.490	L		0.203 (REF)	
E	1.650	-	1.750	J	0.000	-	0.050

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	2.500	-	F6	-	3.100	-
F2	-	2.400	-	F7	-	0.650	-
F3	-	0.450	-	F8	-	0.450	-
F4	-	0.450	-	F9	-	0.500	-
F5	_	2.200	_				

Notes: 1. The suggested land pattern dimensions have been provided for reference only. 2. For further information, please reference document IPC-7351A.

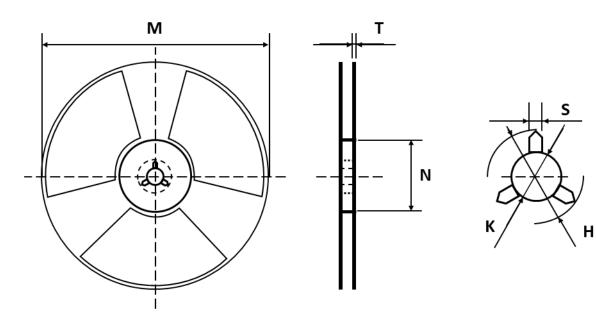
# **ORDERING INFORMATION**

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEC3P07A	DFN 3x3	Reel	3,000pcs	6,000pcs	48,000pcs



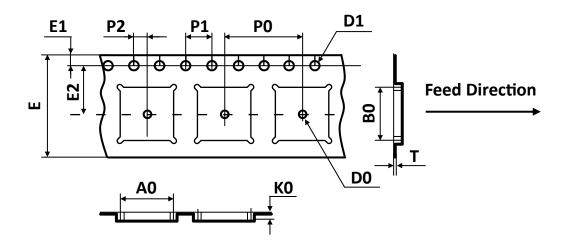


## **REEL DIMENSIONS** All dimensions in mm



Tape Size	Reel Size	М	N	т	н	К	S
12mm	Ø330	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
1211111	Ø550	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

# **TAPE DIMENSIONS** All dimensions in mm



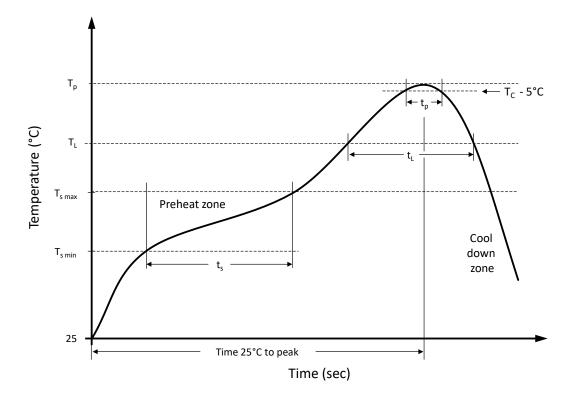
Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
DFN 3x3	3.30	3.30	1.10	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.23
	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.





# **RECOMMENDED REFLOW SOLDERING PROFILE**



## **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes

CEC3P07A ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 8 Copyright by MGT ▲ www.mgt.co.com ▲ All rights reserved ▲ The information in this document is subject to change without notice.



# **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

# DISCLAIMER

Except for the written expressed warranties, MGT does not implicitly, by assumption or whatever else, warrant, under-take, promise any other warranty or guaranty for any MGT product.

All information and technical specifications made available by MGT are for guidance only and we reserve the right to change or modify them without prior notice. Unless expressly stated in writing by MGT, we reject any guarantees, obligations, or warranties.

All MGT products with the technical specifications described are suitable for use in certain applications. Operating, production, storage and environmental conditions can have a massive influence on the parameters mentioned in the data sheets, which cause the performance to vary over time.

It is subject to the user's duty of care to design and validate his products in such a way that appropriate measures are taken, such as protective circuits or redundant systems to ensure the safety standards required in the application.

MGT components are not designed or rated for use in life support, rescue, safety critical, military, or aerospace applications where failure or malfunction could result in property or environmental damage, serious injury or death. In the aforementioned cases, please contact us before using MGT products.

In principle, we reserve all rights and MGT's general terms and conditions apply. You can find them on our website <u>www.mgt.co.com.</u>